Extrinsic inhom ogeneity e ects in m agnetic, transport and m agnetoresistive properties of $La_1 \ _xC a_xM \ nO_3$ (x 0:33) crystal prepared by the oating zone m ethod

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A bstract

The magnetic, transport and magnetoresistive properties of $La_{1 \times} Ca_{x} M nO_{3}$ (x 0:33) crystals prepared by the oating-zone method are studied. In general, these properties testify to rather good crystal perfection of the sample studied. In particular, a huge magnetoresistance (\mathbb{R} (0) R (H))=R (H) in the eld H = 5 T is about

2680 %) is found near the Curie temperature (216 K). At the same time, some distinct features of measured properties indicate the in uence of extrinsic inhom ogeneities arising due to technological factors in the sample preparation. A nalysis of the data obtained shows that these are rare grain boundaries and twins.

Key words: m anganites, colossalm agnetoresistance, m agnetically ordered m aterials, m agnetic inhom ogeneities PACS: 75.47 Gk; 75.47 Lx

1 Introduction

The structural, magnetic and electron transport properties of mixed-valence manganites of the type $R_{1 x} A_x M nO_3$ (where R is a rare-earth element, A

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a divalent alkaline-earth element) attracted much attention in the scienti c community in the last decade (see reviews [1{6]). The interest is caused by observation of huge negative magnetoresistance (MR) near the Curie temperature, T_c, of the param agnetic ferrom agnetic transition for m anganites with 0.5. This phenom enon called \colossal" m agnetoresistance (CMR), 02х is expected to have application in advanced technology. The unique properties of m ixed-valence m anganites are determ ined by the com plex spin, charge and orbital ordered phases, and, therefore, are of great fundam ental interest for physics of strongly correlated electrons. At present, it is believed that one of the key features of manganites is their intrinsic inhom ogeneities in the form of coexisting, competing ferrom agnetic and antiferom agnetic/param agnetic phases [3,4,6]. This phenom enon is generally called \phase separation". The known experim ental studies give num erous (but predom inantly indirect) evidence of structural and m agnetic inhom ogeneities in m anganites, but it hardly can be said that they are intrinsic in all cases. The point is that in all manganites extrinsic inhom ogeneities are inevitably present (even in single crystal sam ples). The inhom openeities of this type arise due to various technological factors in the sample preparation. They can cause chem ical-composition inhom ogeneity (rst of all in the oxygen content), structural inhom ogeneities (polycrystalline or even granular structure), strain inhom ogeneities and so on. It is easy to nd in the literature many experimental studies in which nding of phase separation e ects is proclaimed, but the interpretations are offen doubtful. In such cases the e ects of technological inhom ogeneities are quite obvious or, at least, cannot be excluded.

The experimental data demonstrate that technological inhom ogeneities are unavoidable for any preparation method [7]. For this reason, in many cases it is better to speak about multiphase coexistence instead of the phase separation. It is quite reasonable, therefore, that consideration of experimental data form ixed-valence manganites and development of theoretical models for them take into account the unavoidable in uence of extrinsic disorder and inhom ogeneity. These inhom ogeneities can act separately as well as together with the intrinsic inhom ogeneities (phase separation) and determine to a great extent the magnetic and magnetotransport properties of these compounds.

In this article we present a study of structure, m agnetic, and m agnetoresistive properties of crystals with nom inal composition $La_{0:67}Ca_{0:33}M$ nO₃ prepared by the oating zone m ethod. The m easured properties generally indicate that the sam ple studied is of rather high crystal perfection. At the sam e time som e features of the transport properties rect the essential in uence of extrinsic structural inhom ogeneities arising due to technological factors in the sam ple preparation.

2 Experimental

C rystals of nom inal composition $La_{0:67}Ca_{0:33}M nO_3$ were grown by the oating zone m ethod at the Institute of Physics, W arsaw. The appropriate amounts of starting m aterials La_2O_3 , $CaCO_3$ and $M nO_2$ were calcined at 1000 C, then m ixed, compacted into pellets and sintered at 1400 C. Subsequently, the pellets were m illed, and the resulting powder was then pressed to form the feed rod w ith a diam eter of 8 mm and a length of 90 mm. This rod was further sintered at 1470 C for 12 h in air. An optical fumace (type URN -2-3Pm m ade by M oscow Power Engineering Institute) with two ellipsoidal m irrors and a 2500 W xenon lamp as the heat source was used for crystallization. The feed rod and the growing crystal were rotated in opposite directions to m ake heating uniform and to force convection in the melting zone. The grow th rate was 1 mm/h. An additional afterheater was used for lowering the temperature gradients in the growing crystal.

As shown by previous experience [B], manganite crystals produced by this technique are almost single crystals, and, in this respect, they have far better crystal quality and far less porosity than samples prepared by a solid-state reaction technique. On the other hand, the crystals have tw in dom ain structure and m ay have a few grain boundaries. This question will be discussed more thoroughly below.

The disc-shaped sample for investigation was cut from the middle part of the cylindrical crystal (about 8 mm in diameter). It is known [9,10] that La_{1 x} Ca_xM nO₃ crystals grown by the oating zone technique have an inhom ogeneous distribution of La and Ca along the growth direction. The initial part of the crystal is usually somewhat enriched in La and depleted in Ca. The microprobe elem ental analysis has shown that the sample studied has a chem ical com position close to the nom inal one. This is supported by its transport and m agnetic properties as well, as described below. The sam ple characterization and m easurem ents were done by a variety of experim ental techniques. C rystal structure was determined by the X-ray di raction (XRD) method. The XRD spectra (from powders and bulk pieces taken from the crystal) were obtained using a Rigakum odelD-MAX-B di ractom eter with a graphitem onochrom ator and CuK 1:2 radiation. The ac susceptibility and dcm agnetization were m easured in a Lake Shore m odel 7229 Susceptom eter/M agnetom eter. Resistance as a function of temperature and magnetic eld was measured using a standard four-point probe technique in magnetic elds up to 5 T.

3 Results and discussion

3.1 X-ray di raction study

Bulk La_{1 x} C a_xM nO₃ has a distorted perovskite structure, which is believed to be orthorhom bic below about 750 K [5,11{14]. The deform ation of the cubic perovskite lattice is determ ined by rotation of M nO₆ octahedra and the Jan-Teller distortion [5,14]. For the concentration range 0.25 < x < 0.5, Jan-Teller distortion is found to be negligible [12,14]. In the orthorhom bic space group Pnm a, lattice constants are a $2a_p$, b $2a_p$, and c $2a_p$, where a_p is the lattice constant of the pseudo-cubic perovskite lattice. The symmetry of distortions is, how ever, still a matter of som e controversy [15]. In som e studies a monoclinic lattice is found [15,16]. Generally, how ever, the deviations from cubic symmetry are found to be fairly sm all, especially in the CM R range (0.2 < x < 0.5). Several scienti c groups have found only cubic symmetry in this compound with lattice parameter a_p in the range 0.385-0.388 nm for 0.2 < x < 0.5 (see, for example, Refs. [17,18]).

In this study, XRD investigation was used (along with otherm ethods) to judge the crystal perfection and structural hom openeity of the sam ples. The x-ray spectra from powders and bulk sections of di erent parts of the crystal were measured.We found that XRD powder patterns from the outer and inner parts of the crystal are quite di erent. The positions of all intense and wellde ned lines for the outer part of the crystal are exactly consistent (within the uncertainty of the XRD recording) with those of perfect cubic perovskite¹.A lattice constant $a_p = 0.38713$ nm was computed with the corresponding unit cell volum e v_p 0:0580 nm³. An application of the Pow dercell program [19], which takes into account not only positions, but intensities and pro les of the lines as well, has shown that an orthorhom bic Pnm a lattice also corresponds fairly well to the experimental XRD powder pattern. This gives the lattice constants a = 0.54849 nm, b = 0.77587 nm, and c = 0.54645 nm with a unit $cell volum e v_{o}$ 0.2322 nm^3 .

A quite di erent XRD powder pattern was obtained for inner part of the crystal (Fig. 1). In low resolution this pattern looks the same as that for the outer part of the crystal, but closer inspection shows that most of the lines are split (into two, three, or even four closely located lines). Signi cant line splitting with a severely distorted cubic perovskite lattice was found previously in low doped LaM nO₃ with M n⁴⁺ (or Ca) concentration in the range 0-25 % [16], which was attributed to monoclinic distortions. Splitting due to sm all orthorhom bic distortions for the Ca concentration range 0.25 < x < 0.5 is

¹ The typical linew idth (on the half of the m agnitude) of the m ost intensive lines is found to be in the range of $0.3\{0.4 \text{ degree}$. The step of the XRD pattern recording w as 0.03 degree, that perm itted to record surely the line pro les and reveal available line splitting, which was really found in the inner part of the crystal, as it is shown below.

usually very narrow, so that it cannot be observed clearly (only some line broadening can be seen) [11,20,21].

The splitting of the Bragg re ections could be also ascribed to twinning, which is quite common in mixed-valence manganites. O rigin of twinning in perovskite crystals is well known [14]. At high tem peratures (above about 900 C) La_{1 x} Ca_xM nO₃ (0:2 < x < 0.5) has a cubic perovskite lattice [21]. W hen cooling, the cubic-orthorhom bic (or even cubic-m onoclinic) transition takes place, during which M nO 6 octahedra are rotated and distorted [14]. Since di erent directions of rotation with respect to the original cubic axes are possible, most $La_{1 \times} Ca_{\times} M nO_{3}$ single crystals are twinned. In this case additional re ections (line splitting) can appear if lattices in twin dom ains do not coincide. This can take place in the case of monoclinic distortions [14] or owing to other reasons (for example, when inhom ogeneous strains are present). It is in possible, however, on the basis of powder di raction data to see splitting due to twinning [14]. Only special methods of single-crystal x-ray di raction have opportunities to reveal twinning e ects in manganites [14,22]. But the line splitting in a powder XRD pattern due to considerable distortions from the cubic symmetry is quite possible.

We have applied the above-mentioned Pow dercell program to the XRD data for inner part of the crystal. A ssum ing that crystal lattice is orthorhom bic, we obtained lattice constants a = 0.54972 nm, b = 0.77801 nm, and c = 0.54551 nm with a unit cell volum e v_0 0.2332 nm^3 , but agreement between the calculated and experimental XRD patterns is far worse in this case than that for the outer part of the crystal. It appears therefore that distortions from cubic symmetry are more severe than orthorhom bic ones and they can be monoclinic as it was found in some manganites in Refs. [15,16,22]. This suggestion has found a partial support after application of a M onte C arlo program M dM aille V 3.04 [23] to the experimental XRD data. This has show n rather convincingly that monoclinic lattice is much better corresponds to the XRD data of the inner part of the sample than orthorhom bic lattice.

X-ray study with a Laue cam era revealed that the XRD pattern of a small piece taken from the central part of the sam ple corresponds to a single crystal structure. Investigation with an optical microscope has shown, how ever, that the sam ple as a whole is not a single crystal but consists of a few grains.

3.2 Magnetic properties

D istinctions between the XRD patterns for outer and inner parts of the crystal studied in ply that their magnetic properties can be di erent as well. That is indeed found in this study. The tem perature behavior of the ac susceptibility is presented in Fig. 2. It is seen that the magnetic transition from the param agnetic (PM) to the ferrom agnetic (FM) state with decreasing temperature is considerably smeared for the outer part of the crystal indicating that this part is rather disordered. In contrast to this, the magnetic transition in the central part of the sample is fairly sharp, indicating a signi cant crystal perfection and stoichiom etric hom ogeneity for this part. The same conclusion can be arrived from comparison of the temperature dependences of the dc magnetization, M (T), from which only that for central part of the sample is shown in Fig. 3.

Taking T_c as the temperature of the in ection point in the M (T) curve, we found that T_c 216 K. Nearly the same value can be obtained if T_c were de ned as the temperature at which M comes to half of the maximum value. This T_c value (216 K) is less than that (T_c 250 K) usually found in polycrystalline ceram ic samples in La_{1 x} Ca_xM nO₃ with 0:3 < x < 0:35, and which is indicated in the accepted phase diagram for this system [5]. This value agrees, how ever, well with those found in single crystal samples of the same composition, where T_c values are usually found to be in the range 216{230 K [24{28], although some rare exceptions are known as well [29].

The inset in Fig. 3 shows the magnetic eld dependence of the magnetization at T = 10 K. It is seen that the magnetization is close to saturation above the 0:3 T.W e have recorded M (H) dependences for other tem peratures eld H as well in the range 4{51 K and at elds up to 9 T. Taking the saturation value of M (95.3 em u/g) at the highest eld (9 T) in low temperature range, we have obtained the magnetic moment per form ula unit in the sample studied to be equal to $f_{\rm H}$ 3.65 $_{\rm B}$, where $_{\rm B}$ is the Bohrm agneton. For the nom inal composition $La_{1x} Ca_x M nO_3$ (x = 0.33) of the sample studied, taking into account that the spin of M n⁺³ is S = 2 and that of the M n⁺⁴ is S = 3=2, fu should be equal to $(4 \times)_{B}$, that is to 3.67 _B. The value of _{fu} 3:65 $_{\rm B}$ obtained provides evidence that the inner part of the sample is close to the nom inal composition and does not have any appreciable oxygen de ciency. Since the innerpart of the sample appears to be more hom ogeneous and perfect than the outer part, resistive and magnetoresistive measurements were done for inner part of the sam ple only.

3.3 Resistive and magnetoresistive properties

Tem perature dependences of the resistivity, , and MR, $_0 = \mathbb{R}(H) \mathbb{R}(0) \models \mathbb{R}(0)$, at di erent applied elds, are shown in Figs. 4 and 5. Consider rst the (T) behavior (Fig. 4) which appears som ewhat complicated. In doing so it is appropriate to take a look at the behavior of the tem perature coe cient of resistivity (TCR) [de ned as (1=R)(dR=dT)] as well. This is presented in Fig. 6.

A lthough the (T) behavior relects, generally, a rather high perfection of the crystal studied, some quite distinct features in it should be attributed to the in uence of structural and m agnetic inhom ogeneities. The (T) curve has two peaks, a sharp one at T_p 225 K, which is near the Curie temperature T_c 216 K, obtained from m agnetization and susceptibility studies (Figs. 2 and 3) and a far less pronounced one at T_{pin} 190 K. Additionally, (T) exhibits two shallow m inim a, one is situated at T_{min}° 201 K between the two peaks, and another in the low-temperature range at T_{min}° 16 K (see inset in Fig. 4).

Above T_{c} , the sample is a PM non-metal with an activated temperature dependence of resistivity, following (T) / $\exp(E_a=T)$. The activation energy E_a is found to be equal to 0.09 eV in agreement with that (about 0.1 eV) reported by other authors for single crystal and ceram ic samples of $La_{1 x} Ca_{x} M nO_{3}$ (x 0:33) [17,24,25,30]. It is known [1{3] that the conductivity of Ca-m anganites increases enormously at the transition to the FM state. 0:5), the PM-FM transition occurs simulta-In the La_{1 x} C a_x M nO $_3$ (0.2) Х neously with the insulatorm etalone. For this reason, the (T) dependence has a peak at a tem perature T_p . In samples with fairly perfect crystalline structure, $T_{\rm p}$ is close to $T_{\rm c}$. This is true to a considerable degree for the sample studied . O ther important measures of crystal perfection in manganites are the ratio of the peak resistivity, (T_p) , and the residual resistivity at low tem perature, (0). The value of $(T_{0})=$ (0) is about 200 for the sample studied. This is a high value, com parable with that of single crystals and epitaxial In s of the

high value, com parable with that of single crystals and epitaxial Im s of the best quality [2,24,25,30{32]. For ceram ic samples, prepared by the solid-state reaction method, the ratio $(T_p)=(0)$ is usually far less (see Refs. [5,17,18]. It is well known that samples prepared by the oating-zone method generally have a much sharper resistive transition on going from the PM to FM state than is observed for manganite Im s (com pare data in Refs. [2,24,25,30{32}). This is so indeed in the sample studied which has an extrem ely sharp resistive transition near T_c (Fig. 4). This can be further illustrated by the tem perature behavior of TCR (Fig. 6). The highest value of TCR near T_c found in this study is about 38 % /K; whereas, no more than about 10 % /K is found in the best quality La_{1 x} Ca_xM nO₃ (x 0:3) Im s [32,33].

A long with general characteristics indicating a rather good crystal perfection, the (T) behavior reveals, at the same time, some features which are determined by sample inhom ogeneities (structural and magnetic). These are the second resistance peak at T_{pin} 190 K and the shallow resistance minimum in the low-temperature range. Consider possible reasons for this behavior. It is believed presently that the PM-FM transition in La_{1 x} Ca_xM nO₃ is of rst order at 0.25 < x < 0.4 (see Ref. [7] and references therein). It is found as well that FM clusters are present well above T_c . This in plies that the PM-FM transition has a percolative character.W ith decreasing temperature, the PM volume fraction decreases and that of the FM fraction increases. Since the PM phase is insulating and the FM one is metallic, some kind of insulator-metal transition takes place near T_c . The temperature T_p corresponds to the situation when metallic FM clusters have merged together in a su cient degree to ensure a decrease in resistance with further temperature decrease. This temperature indicates a transition from the insulating to the metallic state and, therefore, is called conventionally the temperature of the insulator-metal transition. Below T_p , the volume of the PM phase continues to decrease with temperature causing a further resistivity decreasing. The temperature width of this type of transition depends in crucial way on the sam ple extrinsic inhom ogeneities induced by various technological factors during the sam ple preparation (see Sec. 1 and R ef. [7]). In sam ples, prepared by the coating-zone method, these inhom ogeneities are determined by mosaic blocks, twins, inhom ogeneous strains, and stoichim etric disorder. These defects are present even in single-crystal C a-m anganites [9,14,34].

Double-peaked (or should ered) (T) curves similar to that shown in Fig. 4 were often seen in polycrystalline manganite samples [30,35{38]. In all cases this behavior was quite reasonably attributed to the in uence of grain boundaries. The evident idea is that regions near the grain boundaries are disordered and even depleted in charge carriers compared with that inside the grains [37,38]. This was supported by direct experiments [39,40], which have shown that grain boundary regions (with thickness of the order 10 nm) have a sm aller T_c than that in the core of the grain. For this reason, when the cores of the grains become FM below T_c, the grain boundary regions still remain in the param agnetic, insulating state, presenting barriers to the transport current. This prevents the form ation of an in nite FM cluster and causes an increase in resistance with decreasing temperature when the FM transition in cores of the grains is completed. The further decrease in temperature, however, leads to a reduction of magnetic disorder in the grain-boundary regions, eliminating som e insulating barriers. If this process proceeds su ciently, (T) behavior becom es m etallic again with the result that a second peak (or shoulder) appears (T). This peak indicates the appearance of the in nite FM cluster. in

The second peak at $T = T_{pin}$ in (T) curve (Fig. 4) suggests the presence of some grain-boundary-like inhom ogeneities in the crystal studied. As a result the (T) dependence shown in Fig. 4 recets actually two resistive transitions in the sample studied. The rst is connected with PM-FM transition inside the grains, while the second one signiles the magnetic ordering of grain-boundary regions. On that ground the second peak position at $T = T_{pin}$ 190 K can be taken as a rough estimate of the Curie temperature T_{cg} of the intergrain regions.

It should be noted that for weak intergrain connectivity (as often takes place in ceram ic samples) the second resistance peak can be rather large and even higher than the rst peak (caused by the intragrain FM transition) [35,38]. Since the second peak is rather weak for the sample studied, it can be said that grain-boundary-like inhom ogeneities are not as strong in it as in ceram ic samples.W hat can be the sources of such inhom ogeneities in samples prepared by the oating-zonem ethod? First of all, som e rare grain boundaries cannot be excluded in this type of sample [30]. But them a jor reason is that these sam ples contain inevitably mosaic blocks and tw in dom ains [14,34]. Tw in boundaries act electively in the same way as grain boundaries, presenting tunnel barriers [34]. The tw ins are present even in polycrystalline m anganites prepared by the solid-state reaction m ethod, where large enough grains (a few m icrons in size) contain multiple tw ins [41].

If the second peak in (T) is determined by the grain-boundary-like interlayers with Curie temperature dimension that inside the grains, it must be depressed by an applied magnetic eld. This really occurs (see Fig. 4). At the same time no visible features associated with grain boundaries can be seen in the M (T) dependence (Fig. 3). This is reasonable if the volume fraction of the grain boundaries is summittee circle of the same all.

When the FM transition in grain/tw in boundary regions is completed, the boundaries can still exert an in uence on the sample conductivity. These boundary regions are places of not only magnetic, but also structural disorder, where charge carriers can be scattered. W hat's more, grain boundaries appear as natural places for FM dom ain boundaries. On the basis of the known experimental data [39,40] the follow ing model of grain boundaries in the manganites can be assumed. A transition region between any two grains consists of two layers depleted of charge carriers (and having a reduced Curie tem – perature T_{cg}) and some thin (thickness about a nanom eter) insulating layer between them . The latter presents the tunnel barriers for the charge carriers even at low tem perature $T < T_{cg}$ when the two depleted layers become a ferrom agnetic and, most likely, metallic. It is quite reasonable to assume that the thickness of the insulating layers (tunnel barriers) is not the same throughout the sample, so the system is percolating in this context as well.

Q uantum tunneling of the charge carriers occurs between states of equal energy. A ctually, however, there is always some energy level m ism atch between states in neighboring grains for dierent reasons. In this case, a charge carrier should gain some energy (for example, from phonons) to accomplish tunneling. The intergrain conductivity is conditioned, therefore, by the two processes: the tunneling and therm all activation. If the activation energy of tunneling, E_t , is rather low, then tunneling at high enough temperature, $kT > E_t$, is non-activated. In that event the system behaves like a metal (dR =dT > 0). Since the grain boundary thickness is not the same throughout the system, the conductivity is percolating. It is determined by the presence of \optim all' chains of grains with maximum probability of tunneling for adjacent pairs of

grains form ing the chain. These \optim al" chains have some weak links (high-resistance tunnel junctions). At low enough tem perature the relation kT < E_t can become true for such links, and, hence, the measured conductivity of the system will become activated. This is an evident reason for the observed resistance minimum at $T_{m in}^{\infty}$ 16 K (Fig. 4). More generally it can be said that the minimum is determined by competition between the intragrain conductivity ity and the intergrain tunneling. The low-tem perature resistance minimum is typical for systems of FM regions with rather weak interconnections. It has been observed in polycrystalline [42] and even single crystal [34] sam ples. We found that an applied magnetic eld has no noticeable elect on the resistance minimum position. This may signify that the tunnel barriers are non-magnetic in the low temperature range.

It follows from discussion above that the double-peaked feature and the low tem perature resistance minimum in (I) of the sample studied can be adequately explained by the in uence of the grain/twin boundaries. The measured tem perature dependences of MR (Fig. 5) re ect the in uence of these structural inhom ogeneities as well. Generally, the M R in manganites is determ ined by intrinsic and extrinsic causes. The CMR is an intrinsic e ect determ ined by the ability of an external magnetic eld to increase the magnetization. It is clear that at low tem perature (T T_c) when all spins are already aligned by the exchange interaction, this ability is minimal. The possibility to strengthen the magnetic order with an external magnetic eld increases profoundly near T_c where the magnetic order becomes weaker. For this reason, CMR is maxin al near T_c and goes to nearly zero value for T T_c . This behavior is unique to bulk or Im manganites of rather good crystal perfection [30,33]. The presence of extrinsic inhomogeneities (such as grain boundaries) gives rise to an extrinsic MR e ect. Considering Fig. 5, it is safe to assume that the sharp MR peak at T 220 K is caused by CMR; whereas, the rather weak 173 K is connected with the in uence of grain/twin boundaries. peak at T The measured temperature behaviors of the MR (Fig. 5) and the resistance (Fig. 4) are clearly correlated and both of them re ect the in uence of extrinsic inhom openeities. At the same time, they also dem onstrate the good crystal perfection of the sample. Really, the maximum value of MR, expressed as $_0 = \mathbb{R}(H) = \mathbb{R}(0) = \mathbb{R}(0)$, is about -96.4 % near the Curie tem perature in a 5 Т eld. This is the CMR indeed. Since o, by de nition, cannot be higher than 100 %, another characterization of CMR, namely, $_{\rm H} = [R (0)]$ R (H)]=R (H) is frequently used. In the crystal studied, the maximum $_{\rm H}$ in the 5 T $\,$ ed is 2680 % . This is even higher than the MR found in some single-crystal about Ca-manganites of the nearly same chemical composition (see Ref. [25]). In ceram ic samples, however, the values of $_{\rm H}$ are usually about two orders of the m agnitude less [17,35,39].

It is known that a contribution to MR coming from grain-boundary-like inhom ogeneities increases with decreasing temperature. D iscussion of the possible m echanisms for this extrinsic type of the MR can be found in Refs. [43[46]. The sample studied does indeed show a continuous increase in MR with decreasing temperature in a 0.5 T eld in the temperature range below 200 K (Fig. 5). In higher elds, the MR behavior is more complicated. It should be noted that the temperature behavior of MR and its changes with increasing applied magnetic eld, revealed in the sample studied (Fig. 5), are quite sim – ilar to that found in Ref. [30] for the MR of a single grain boundary in a Ca-m anganite crystal grown by the oating-zone method. This suggests once again that grain/tw in boundaries in the sample studied are not large in num – ber.

It is well established [43{47] also that the extrinsic M R connected with grain boundaries has one m ore characteristic feature. In the low – eld region (H < H_s, where H_s is a characteristic eld) the resistance decreases rapidly with increasing H [so called, low – eld M R (LFM R)]. For H > H_s, the resistance changes m ore gradually [high – eld M R (HFM R)]. In both these eld regions, the resistance changes alm ost linearly with H. The LFM R is found to decrease rather rapidly with increasing tem perature so that the broken-line type of the R (H) dependence is changed to a sm ooth featureless dependence for higher tem perature. All these features of extrinsic M R can be seen in Fig. 7, where M R vs H for two tem peratures (4.2 K and 68 K) is presented. In the know n studies ofm anganites the characteristic eld H_s is typically below 0.5 T and is attributed to the eld ofm agnetic dom ain rotation (when the m agnetization m agnitude com es close to the technical saturation value). This corresponds roughly to the dependence of M (H) shown in the inset to Fig. 3.

It is currently believed [44,46,47] that the grain-boundary M R in m anganites is determ ined primarily by the spin-dependent tunneling of charge carriers between the grains. The LFM R is attributed to m agnetic alignment of the grains; whereas, HFM R to an increase in the spontaneous m agnetization in higher eld. For the low temperature range the latter process occurs m ainly within the disordered grain-boundary regions, while for high enough temperature it takes place m ainly inside the grains causing CM R. This competition of CM R and the extrinsic M R gives a som ewhat intricate picture of the total M R behavior found in this study. W e will not consider further these or other peculiarities of the extrinsic M R connected with grain-boundary-like inhom ogeneities nor the corresponding possible m echanisms of this behavior. It is clear enough from the data obtained that the sam ple studied contains inhom ogeneities of this type.

In conclusion, we have studied structure, m agnetic, and m agnetoresistive properties of crystals with nom inal composition $La_{0:67}Ca_{0:33}M$ nO₃ prepared by the oating zone m ethod. The properties indicate undoubtedly that the sam ple is of fairly high crystal perfection. In particular, it has very low resistivity at low temperature and a huge M R near the Curie temperature ($_{\rm H}$ = $[R(0) \quad R(H)]=R(H)$ in the eld H = 5 T is about 2680 %). At the same time, some features of the transport and m agnetoresistive properties reject the essential in uence of extrinsic grain-boundary type structural inhom ogeneities arising due to technological factors in the sample preparation. It is shown that these inhom ogeneities are rare grains and twins.

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- [1] A.P.Ram irez, J.Phys.: Condens M atter 9 (1997) 8171.
- [2] J.M.D.Coey, M.Viret, and S.von Molnar, Adv. Phys. 48 (1999) 167.
- [3] E.Dagotto, T.Hotta, and A.Moreo, Phys. Rep. 344 (2001) 1.
- [4] E.L.Nagaev, Phys.Uspekhi39 (1996) 781; Phys.Rep. 346 (2001) 387.
- [5] K.H. Kim, M. Uehara, V. Kiryukhin, and S-W. Cheong, in Colossal magnetoresistive manganites, T. Chatterji (ed.), Kluwer Academic Publ., Dordrecht, Netherlands (2003); preprint cond-m at/0212113.
- [6] E.Dagotto, J.Burgy, and A.Moreo, Solid State Commun. 126 (2003) 9; E. Dagotto, preprint cond-m at/0302550.
- [7] B. I. Belevtæv, Fiz. Nizk. Temp. 30 (2004) 563 [Low Temp. Phys. 30 (2004) 421]; preprint cond-m at/0308571.
- [8] B.I.Belevtæv, A.Ya.Kirichenko, N.T.Cherpak, G.V.Golubnichaya, I.G. Maxim chuk, E.Yu.Beliayev, A.S.Pan lov, J.Fink-Finowicki, J.Magn.Magn. Mater. 281 (2004) 97; preprint cond-mat/0404131.
- D. Shulyatev, S. Karabashev, A. Arsenov, Ya. Mukovskii, and S. Zverkov, J. Cryst. Growth 237-239 (2002) 810.
- [10] Ya. M. Mukovskii, Rossiiskii Khim. Zh. (Russian Chem. Journ.) XLV (2001) 32.
- [11] P. Dai, Jiandi Zhang, H. A. Mook, S.H. Liou, P. A. Dowben, and E. W. Plummer, Phys. Rev. B 54 (1996) R 3694.
- [12] S. J. Hibble, S. P. Cooper, A. C. Hannon, I. D. Fawcett, and M. Greenblatt, J. Phys.: Cond. Matter 11 (1999) 9221.
- [13] A.Das, K.R. Chakraborty, S.S.Gupta, S.K. Kulshreshtha, and S.K. Paran pe, J.M agn. M ater. 237 (2001) 41.
- [14] Bas B. Van Aken, A. Meetsma, Y. Tomioka, Y. Tokura, and Thomas T. M. Palstra, Phys. Rev. B 66 (2002) 224414; B.B. Van Aken, Ph.D. Thesis, University of Groningen (2001), www.ub.rug.nl/eldoc/dis/science.
- [15] O. I. Lebedev, G. Van Tendeloo, A. M. Abakum ov, S. Am elinckx, B. Leibold, and H.-U. Haberm eier, Phil. Mag. A 79 (1999) 1461.
- [16] E.O.W ollan and W.C.Koehler, Phys. Rev. 100 (1955) 545.
- [17] R. Mahendiran, S. K. Tiwary, A. K. Raychaudhuri, T. V. Ramakrishnan, R. Manesh, N. Rangavittal, and C. N. R. Rao, Phys. Rev. B 53 (1996) 3348.
- [18] R. Laiho, K. G. Lizunov, E. Lahderanta, P. Petrenko, V. N. Stam ov, and V. S. Zakhvalinskii, J. Magn. Magn. Mater. 213 (2000) 271.

- [19] A vailable at http://www.ccp14.ac.uk.
- [20] Y. H. Li, K. A. Thomas, P. S. I. P. N. de Silva, L. F. Cohen, A. Goyal, M. Rajeswari, N. D. Mathur, M. G. Blamire, J. E. Evetts, T. Venkatesan, and J. L. MacManus-Driscoll, J. Mater. Res. 13 (1998) 2161.
- [21] Jiaqing He, Renhui W ang, Jiaian Gui, and Cheng Dong, Phys. Stat. Sol. B 229 (2002) 1145.
- [22] R. Tam azyan, Sander van Sm aalen, A. Arsenov, and Ya. Mukovskii, Phys. Rev. B 66 (2002) 224111.
- [23] A vailable at http://www.cristalorg/m cm aille.
- [24] S.H.Chun, M.B.Salam on, Y.Tom ioka, and Y.Tokura, Phys. Rev. B 61 (2000) R 9225.
- [25] Y. Lyanda-Geller, S. H. Chun, M. B. Salam on, P. M. Goldbart, P. D. Han, Y. Tom ioka, A. A sam itsu, and Y. Tokura, Phys. Rev. B 63 (2001) 184426.
- [26] Chang Seop Hong, W an Seop K in , and N am HwiHur, Phys. Rev. B 63 (2001) 092504.
- [27] H.S.Shin, J.E.Lee, Y.S.Nam, H.L.Ju, and C.W. Park, Solid State Commun. 118 (2001) 377.
- [28] Sheng-Bo T ian, M anh-H uong Phan, Seong-C ho Yu, and N am HwiHur, Physica B 327 (2003) 221.
- [29] C.P.Adams, J.W. Lynn, V.N. Smolyaninova, A.Biswas, R.L.Greene, W. Ratcli II, S-W. Cheong, Y.M. Mukovskii, and D.A. Shulyatev, preprint condmat/0304031.
- [30] B. Vertruyen, R. Cloots, A. Rulmont, G. Dhalenne, M. Ausloos, and Ph. Vanderbern den, J. Appl. Phys. 90 (2001) 5692.
- [31] F. Martin, G. Jakob, W. Westerburg, and H. Adrian, J. Magn. Magn. Mater. 196-197 (1999) 509.
- [32] A.Goyal, M.Rajeswari, R.Shreekala, S.E.Lo and, S.M.Bhagat, T.Boettcher, C.Kwon, R.Ramesh, and T.Venkatesan, Appl. Phys. Lett. 71 (1997) 2535.
- [33] Yu. P. Sukhorukov, E. A. Gan'shina, B. I. Belevtsev, N. N. Loshkareva, A. N. Vinogradov, K. D. D. Rathnayaka, A. Parasiris, and D. G. Naugle, J. Appl. Phys. 91 (2002) 4403.
- [34] Y. Yuzhelevski, V. Markovich, V. Dikovsky, E. Rozenberg, G. Gorodetsky, G. Jung, D. A. Shulyatev, and Ya. M. Mukovskii, Phys. Rev. B 64 (2001) 224428.
- [35]G.H.Rao, J.R.Sun, Y.Z.Sun, Y.L.Zhang, and J.K.Liang, J. Phys.: Condens. M atter 8 (1996) 5393.
- [36] X.L.W ang, P.G ehringer, W. Lang, J.Horvat, H.K.Liu, and S.X.Dou, Solid State Comm. 117, 53 (2001).

- [37] A.D. Hernandez, C. Hart, R. Escudero, O. Ares, Physica B 320 (2002) 64.
- [38] S. Surthi, S. Kotru, R. K. Pandey, P. Fournier, Solid State Comm. 125 (2003) 107.
- [39] A. K. Kar, A. Dhar, S. K. Ray, B. K. Mathur, D. Bhattacharya, and K. L. Chopra, J. Phys.: Condens. Matter 10 (1998) 10795.
- [40] M.Bibes, Ll.Balœlls, J.Fontcuberta, M.Wojcik, S.Nadolski, and E.Jedryka, Appl.Phys.Lett. 82 (2003) 928.
- [41]Q.Chen, J.Tao, J.M. Zuo, and J.C.H. Spence, J.M ater. Res. 16 (2001) 2959.
- [42] A.de Andres, M.Garcia-Hernandez, and J.L.Martinez, Phys. Rev. B 60 (1999) 7328.
- [43] A. Gupta, in Colossal Magnetoresistance, Charge Ordering and Related Properties of Manganese Oxides, C.N.R.Rao and B.Raveau (eds.), World Scientic, Singapore (1998), p.189.
- [44] H.Y.Hwang, S-W.Cheong, N.P.Ong, and B.Batlogg, Phys. Rev. Lett. 77 (1996) 2041.
- [45] J.E.Evetts, M.G.Blamire, N.D.Mathur, S.P.Isaac, B.S.Teo, L.F.Cohen, and J.L.MadManus-Driscoll, Phil. Trans. R. Soc. A 356 (1998) 1593.
- [46] M. Ziese, Rep. Progr. Phys. 65 (2002) 143.
- [47] H.Y.Hwang and S-W. Cheong, in Colossalm agnetoresistive oxides, Y.Tokura (ed.), Gordon and Breach, Singapore (2000), p.307.

Figure captions

Figure 1.XRD powder pattern of the inner part of the crystal with nom inal composition $La_{0:67}Ca_{0:33}M$ nO₃. The indicated indexes correspond to lines for cubic perovskite-like unit cell. It is seen that most of the lines are split. To show this more clearly, the region around the (211) re ection is magni ed in the inset.

Figure 2. Tem perature dependences of the real part, $^{\circ}$, of ac susceptibility for the outer (a) and central (b) parts of the crystal studied. The dependences were recorded (with a 125 Hz ac magnetic eld H_{ac} = 1 10⁵ T) with increasing tem perature after the sam ples were cooled in zero eld.

Figure 3. Tem perature dependences of the magnetization of the central part of the sample recorded (in a dcm agnetic eld $H_{dc} = 0.2 \text{ m T}$) with increasing tem perature after the sample was cooled in zero eld. The inset shows the magnetic eld dependence of the magnetization at T = 10 K.

Figure 4. Tem perature dependences of the resistivity of the sample, recorded in zero magnetic eld and in elds H = 0.5, 1, 2, 3.5 and 5 T. Inset shows a shallow resistance minimum at low temperature. The minimum temperature, T_{min}^{∞} , is about 16 K.

Figure 5. Tem perature dependences of the magnetoresistance of the sample, recorded at di erent magnitudes of applied magnetic eld.

Figure 6.Tem perature behavior of tem perature coe cient of resistance, (1=R)(dR=dT), of the sam ple at zero m agnetic eld.

Figure 7.M agnetic- eld dependences of the magnetoresistance, \mathbb{R} (H) R (O) = R (O), of the sample at T = 4.2 K and 68 K. The dependences were recorded for increasing and subsequently for decreasing applied magnetic eld.No signi cant hysteresis in the curves can be seen.

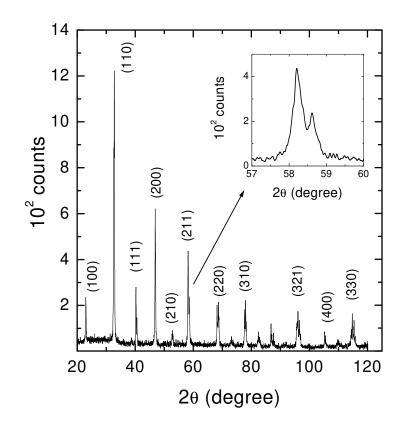


Figure 1 to paper Belevtsev et al.

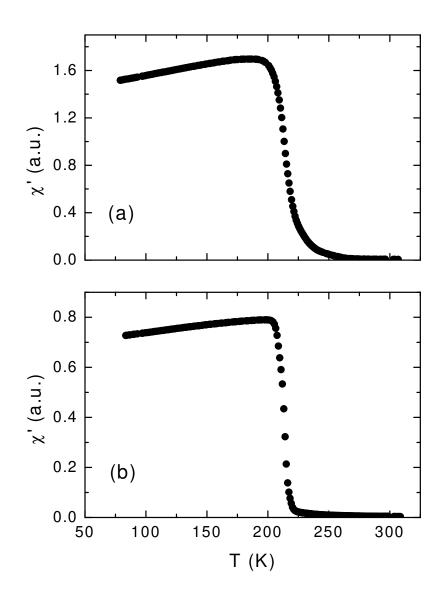


Figure 2 to paper Belevtsev et al.

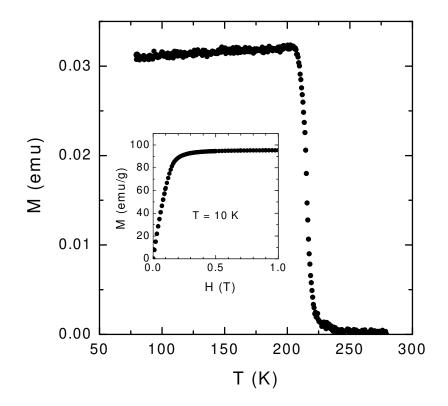


Figure 3 to paper Belevtsev et al.

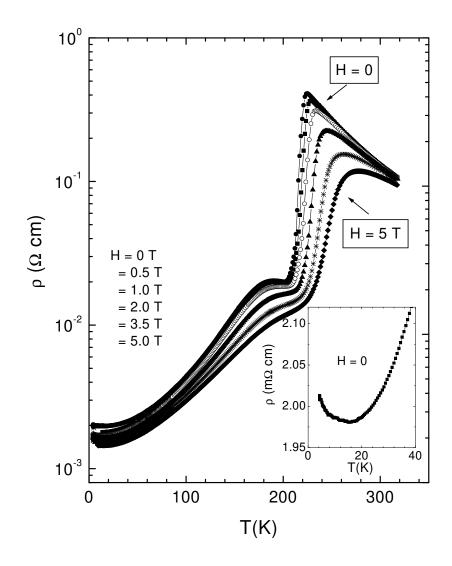


Figure 4 to paper Belevtsev et al.

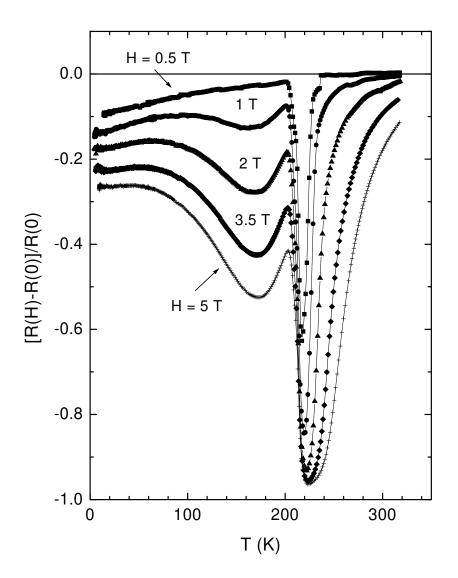


Figure 5 to paper Belevtsev et al.

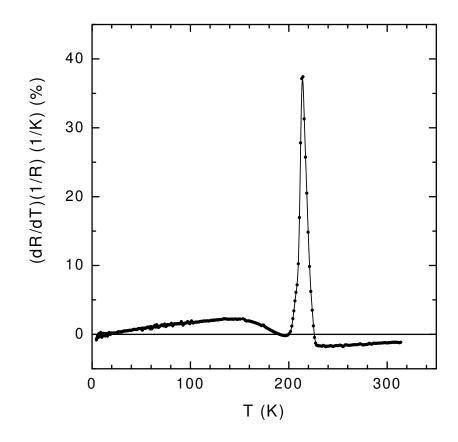


Figure 6 to paper Belevtæv et al.

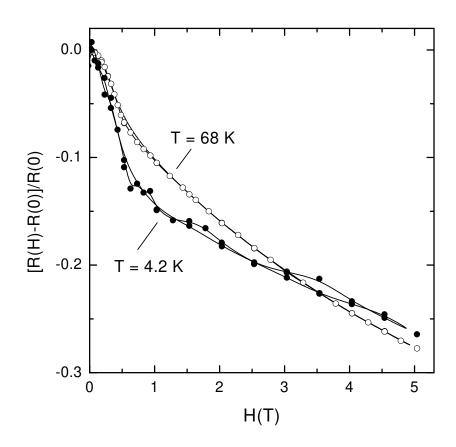


Figure 7 to paper Belevtsev et al.